

NTE6232 Powerblock Module

Description:

The NTE6232 uses 2 power diodes in series and the semiconductors are electrically isolated from the metal base, allowing common heatsinks and compact assemblies to be built. This device is intended for general purpose applications such as battery chargers, welders and plating equipment and where high voltage and high current are required.

Features:

- Standard Voltage
- Electrically Isolated Base Plate
- 3500V_{RMS} Isolating Voltage
- High Surge Capability
- Large Creepage Distances

Ratings and Characteristics:

Average Forward Current ($T_C = +92^\circ\text{C}$, 180° Conduction, Half Sine Wave), $I_{F(AV)}$ 100A
 Maximum RMS On-State Current, $I_{T(RMS)}$ 141A
 Maximum Repetitive Peak Reverse and Off-State Blocking Voltage, V_{RRM} , V_{DRM} 1600V
 Maximum Non-Repetitive Peak Reverse Voltage, V_{RSM} 1700V
 Maximum Peak Reverse Current ($T_J = +125^\circ\text{C}$), I_{RRM} 10mA
 RMS Isolation Voltage (50Hz, Circuit to Base, All Terminals Shorted, $t = 1\text{s}$), V_{ISO} 3500V
 Operating Junction Temperature Range, T_J -40° to $+150^\circ\text{C}$
 Storage Temperature Range, T_{stg} -40° to $+150^\circ\text{C}$
 Thermal Resistance, Junction-to-Case (Per Module, DC Operation), R_{thJC} 0.22°C/W
 Thermal Resistance, Case-to-Sink (Note 1), R_{thCS} 0.1°C/W

Note 1. Mounting surface flat, smooth and greased.

Electrical Specifications:

Parameter	Symbol	Test Conditions		Rating	Unit
Maximum Peak One-Cycle Non-Repetitive Surge Current	I_{FSM}	$t = 10\text{ms}$	Sinusoidal Half Wave, 100% V_{RRM} Reapplied, Initial $T_J = +150^\circ\text{C}$	1700	A
		$t = 8.3\text{ms}$		1780	A
		$t = 10\text{ms}$	Sinusoidal Half Wave, No Voltage Reapplied, Initial $T_J = +150^\circ\text{C}$	2020	A
		$t = 8.3\text{ms}$		2110	A

Electrical Specifications (Cont'd):

Parameter	Symbol	Test Conditions	Rating	Unit
Maximum I^2t for Fusing	I^2t	$t = 10\text{ms}$	14450	A^2s
		$t = 8.3\text{ms}$	13190	A^2s
		$t = 10\text{ms}$	20430	A^2s
		$t = 8.3\text{ms}$	18650	A^2s
Maximum $I^2\sqrt{t}$	$I^2\sqrt{t}$	$t = 0.1$ to 10ms , no voltage reapplied	204300	$\text{A}^2\sqrt{t}$
Threshold Voltage, Low level	$V_{F(TO)1}$	$T_J = +150^\circ\text{C}$, $(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)})$	0.66	V
Threshold Voltage, High level	$V_{F(TO)2}$	$T_J = +150^\circ\text{C}$, $(\pi \times I_{T(AV)} < I < 20 \times \pi \times I_{T(AV)})$	0.74	V
Forward Slope Resistance, Low Level	r_{f1}	$T_J = +150^\circ\text{C}$, $(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)})$	1.81	$\text{m}\Omega$
Forward Slope Resistance, High Level	r_{f2}	$T_J = +150^\circ\text{C}$, $(\pi \times I_{T(AV)} < I < 20 \times \pi \times I_{T(AV)})$	1.57	$\text{m}\Omega$
Maximum Forward Voltage Drop	V_{FM}	$T_J = +25^\circ\text{C}$, $I_{FM} = \pi \times I_{F(AV)}$, Av. Power = $V_{F(TO)} \times I_{T(AV)} + r_f \times (I_{F(RMS)})^2$	1.3	V

Circuit Diagram

